

## 产品概览

### NTHD3101F: P 沟道 ChipFET™ 功率 MOSFET 和肖特基二极管 -20V -4.4A 80mΩ

欲看完整文档，请参阅数据表。

功率 MOSFET -20V -4.4A 80mΩ P 沟道 ChipFET™ 4.1 A 肖特基势垒二极管

#### 特性

- Leadless SMD Package Featuring a MOSFET and Schottky Diode
- 40% Smaller than TSOP-6 Package
- Leadless SMD Package Provides Great Thermal Characteristics
- Independent Pinout to each Device to ease Circuit Design
- Trench P-Channel for Low On Resistance
- Ultra Low VF Schottky

#### 应用

- Li-Ion Battery Charging
- High Side DC-DC Conversion Circuits
- High Side Drive for Small Brushless DC Motors
- Power Management in Portable, Battery Powered Products

#### 器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(BR)}$ Min (V)	$V_{GS}$ Max (V)	$V_{GS(th)}$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5V$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5V$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10V$ (mΩ)	$Q_g$ Typ @ $V_{GS} = 4.5V$ (nC)	$Q_g$ Typ @ $V_{GS} = 10V$ (nC)	$C_{iss}$ Typ (pF)	Package Type
NTHD3101FT1G	0.1733	Pb-free Halide free non AEC-Q and PPAP	Active	P-Channel	with Schottky Diode	-20	8	1.5	3.2	1.1	85	64	-	8.6	7.4	680	Chip FET-8

欲了解更多信息，请联系您当地的销售支援 [www.onsemi.cn](http://www.onsemi.cn)。

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